

ABSTRACT OF THE DISCLOSURE

Embodiments in accordance with the present invention provide for forming floating gate transistor structures as well as the structures so formed. An exemplary method provides a substrate encompassing semiconductive material. A first layer is formed over the semiconductive material. At least one pair of spaced shallow trench isolation (STI) structures are formed extending through the first layer and into the semiconductive material, and at least a portion of the first layer between the spaced STI structures is removed effective to form a recess there between. The recess is at least partially filled by forming a conductive floating gate material therein and a control gate is formed operatively over the conductive floating gate material to form the floating gate transistor.

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